# 2SD1823G

## Silicon NPN epitaxial planar type

#### For low-frequency amplification

#### ■ Features

- High forward current transfer ratio h<sub>FE</sub>
- ullet Low collector-emitter saturation voltage  $V_{CE(sat)}$
- High emitter-base voltage (Collector open) V<sub>EBO</sub>
- Low noise voltage NV
- S-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

### Package

- Code
  - SMini3-F2
- Marking Symbol: 1Z
- Pin Name
  - 1: Base
  - 2: Emitter
- 3: Collector

#### ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	50	V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	40	V
Emitter-base voltage (Collector open)	$V_{EBO}$	15	V
Collector current	I <sub>C</sub>	50	mA
Peak collector current	$I_{CP}$	100	mA
Collector power dissipation	P <sub>C</sub>	150	mW
Junction temperature	$T_{j}$	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

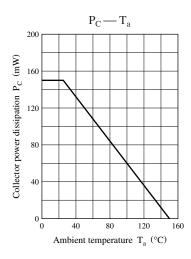
### ■ Electrical Characteristics $T_a = 25$ °C $\pm 3$ °C

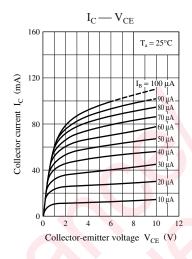
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_C = 10 \mu\text{A}, I_E = 0$	50			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = 1 \text{ mA}, I_B = 0$	40			V
Emitter-base voltage (Collector open)	$V_{EBO}$	$I_E = 10  \mu A, I_C = 0$	15			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 20 \text{ V}, I_{E} = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = 20 \text{ V}, I_{B} = 0$			1	μΑ
Forward current transfer ratio *	$h_{FE}$	$V_{CE} = 10 \text{ V}, I_{C} = 2 \text{ mA}$	400		2000	_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$		0.05	0.20	V
Transition frequency	$f_T$	$V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$		120		MHz

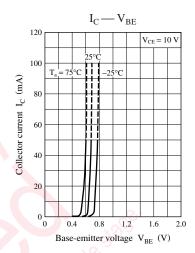
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

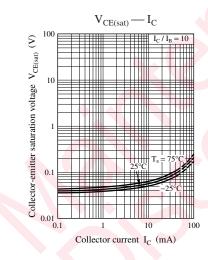
#### 2. \*: Rank classification

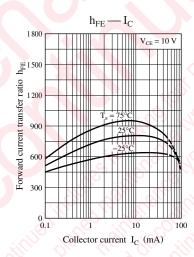
Rank	R	S	Т
$h_{FE}$	400 to 800	600 to 1 200	1000 to 2000

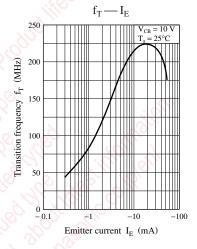


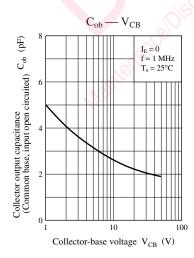


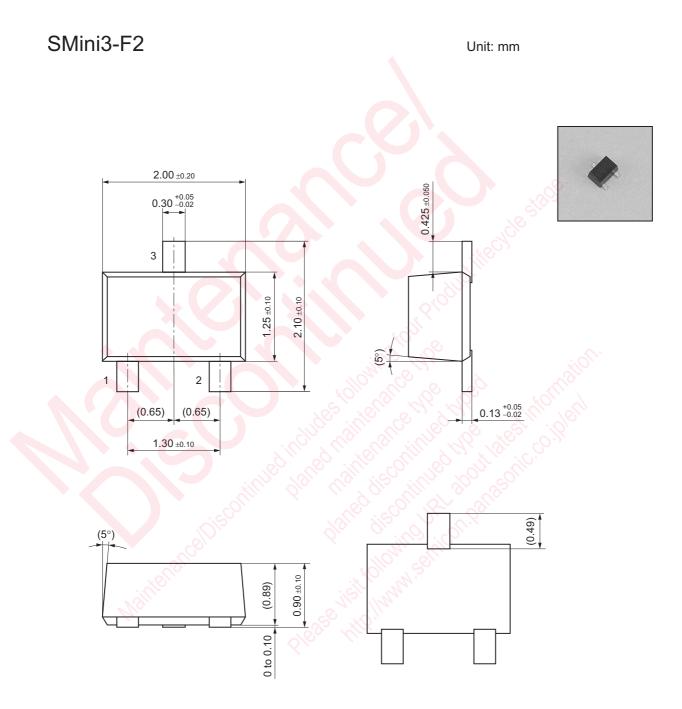












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